

BR2SB1260Q

Rev.A Apr.-2023

描述 / Descriptions

SOT-89 塑封封装 PNP 半导体三极管。Silicon PNP transistor in a SOT-89 Plastic Package.

特征 / Features

击穿电压高，放大线性好，饱和压降低，与 BR2SD1898Q 互补，符合 AEC-Q101 标准高可靠性要求，无卤产品。

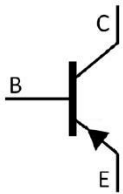
High breakdown voltage, good h_{FE} linearity, low $V_{CE(sat)}$, complements the BR2SD1898Q, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

用途 / Applications

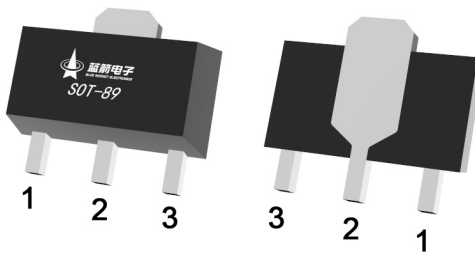
一般功率放大，满足汽车应用的严格要求。

General power amplifier applications, Meet the stringent requirements of automotive applications.

内部等效电路 / Equivalent Circuit



引脚排列 / Pinning



PIN1 : Base

PIN 2 : Collector

PIN 3 : Emitter

放大及印章代码 / h_{FE} Classifications & Marking

h_{FE} Classifications Symbol	P	Q	R
h_{FE} Range	82~180	120~270	180~390
Marking	QBHP*	QBHQ*	QBHR*

极限参数 / Absolute Maximum Ratings(Ta=25°C)

参数 Parameter	符号 Symbol	数值 Rating	单位 Unit
Collector to Base Voltage	V_{CBO}	-80	V
Collector to Emitter Voltage	V_{CEO}	-80	V
Emitter to Base Voltage	V_{EBO}	-5.0	V
Collector Current-Continuous	I_C	-1.0	A
Collector Current-Continuous(Pulse)	$*I_{CP}$	-2.0	A
Collector Power Dissipation	$**P_C$	0.5	W
	$*P_C$	2.0	W
Junction Temperature	T_j	150	°C
Storage Temperature Range	T_{stg}	-55~150	°C

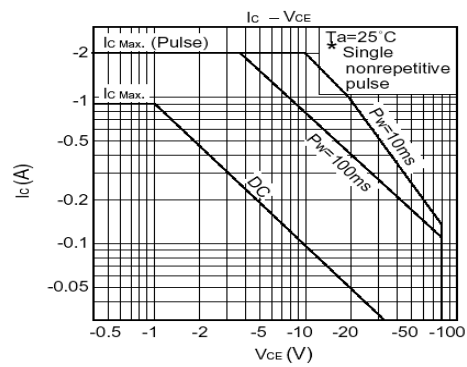
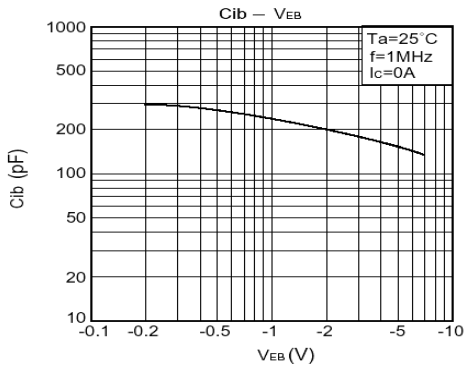
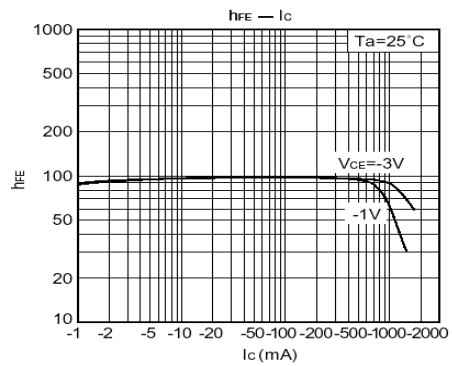
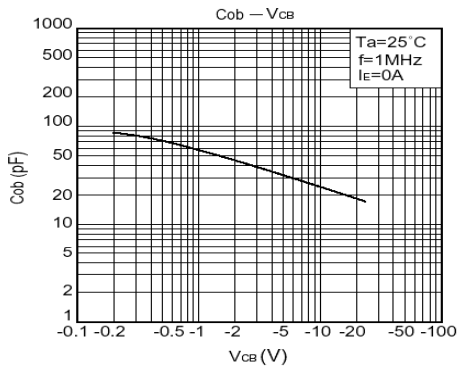
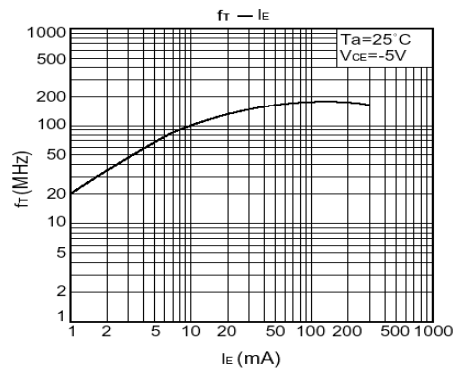
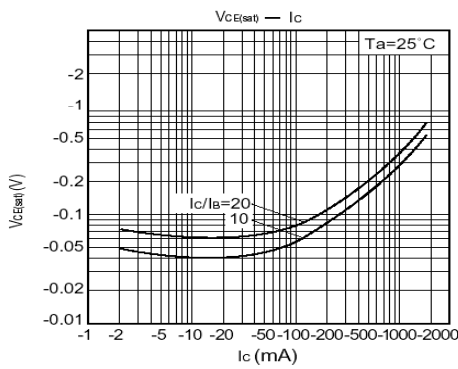
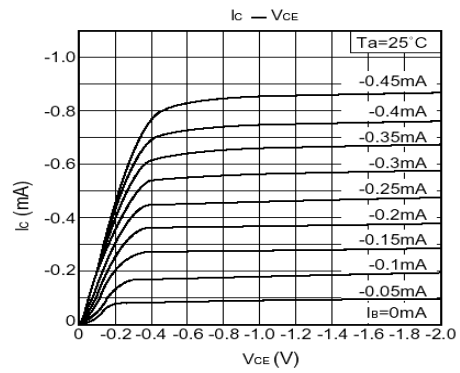
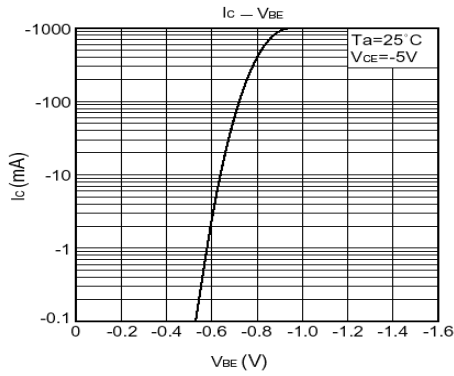
*Single pulse Pw=100ms: 脉冲测试, 脉宽 100ms。

**mounted on 40×40×0.7mm ceramic board: 装于 40×40×0.7m 的陶瓷上。

电性能参数 / Electrical Characteristics(Ta=25°C)

参数 Parameter	符号 Symbol	测试条件 Test Conditions	最小值 Min	典型值 Typ	最大值 Max	单位 Unit
Collector to Base Breakdown Voltage	V_{CBO}	$I_C=-50\mu A$ $I_E=0$	-80			V
Collector to Emitter Breakdown Voltage	V_{CEO}	$I_C=-1.0mA$ $I_B=0$	-80			V
Emitter to Base Breakdown Voltage	V_{EBO}	$I_E=-50\mu A$ $I_C=0$	-5.0			V
Collector Cut-Off Current	I_{CBO}	$V_{CB}=-60V$ $I_E=0$			-1.0	μA
Emitter Base Cut-Off Current	I_{EBO}	$V_{EB}=-4.0V$ $I_C=0$			-1.0	μA
DC Current Gain	h_{FE}	$V_{CE}=-3.0V$ $I_C=-0.1A$	82		390	
Collector to Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=-500mA$ $I_B=-50mA$			-0.4	V
Transition Frequency	f_T	$V_{CE}=-5.0V$ $f=30MHz$ $I_C=-50mA$		100		MHz
Collector Output Capacitance	C_{ob}	$V_{CE}=-10V$ $f=1.0MHz$ $I_E=0$		25		pF

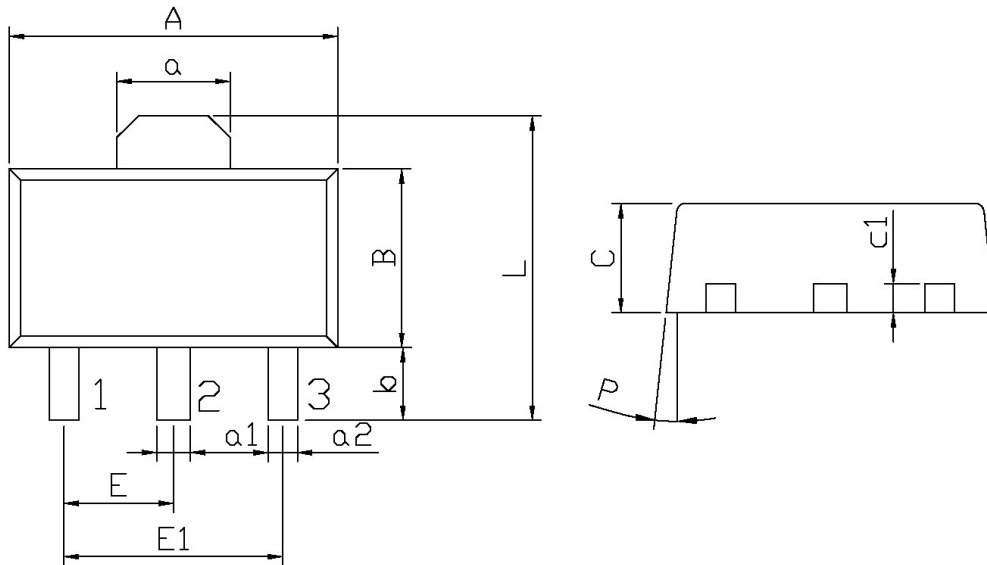
电参数曲线图 / Electrical Characteristic Curve



外形尺寸图 / Package Dimensions

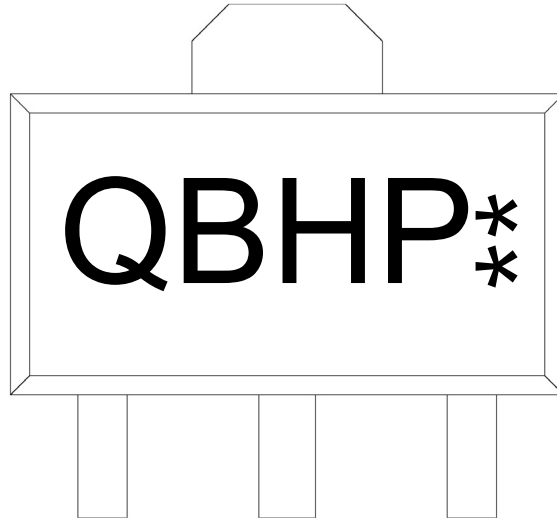
SOT-89

单位: mm



Symbol	Dimensions In Millimeters		Symbol	Dimensions In Millimeters	
	Min	Max		Min	Max
A	4.4	4.7	a1	0.36	0.56
B	2.35	2.65	a2	0.30	0.50
L	3.878	4.478	C	1.40	1.70
a	1.45	1.65	c1	0.35	0.50
E	1.40	1.60	P	6°	
E1	2.80	3.20			
b	0.80	1.20			

印章说明 / Marking Instructions



说明：

Q： 为汽车无卤产品标识

BH： 为型号代码

P： 为 hFE 分档代码

**： 为生产批号代码，随生产批号变化

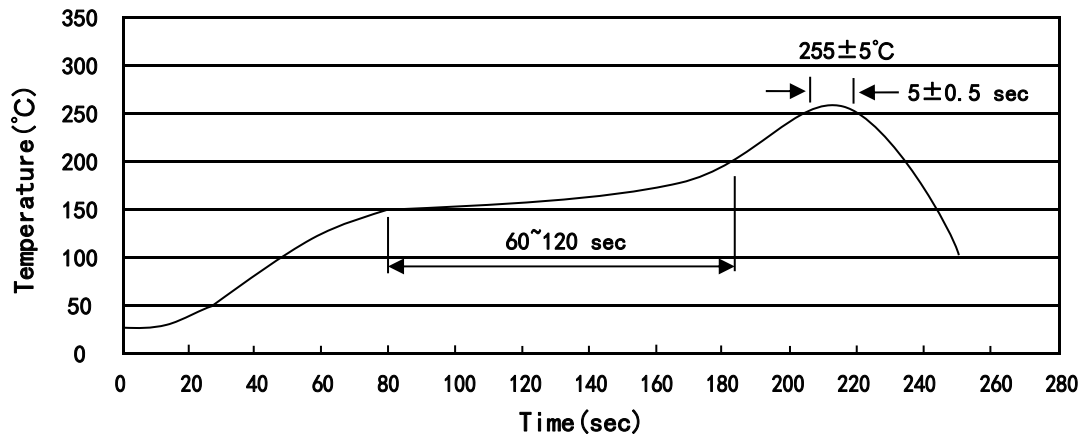
Note:

Q: Automobile halogen-free product Code

BH: Product Type

P: hFE Classifications Symbol

** : Lot No. Code, code change with Lot No

回流焊温度曲线图(无铅) / Temperature Profile for IR Reflow Soldering(Pb-Free)


说明：

- 1、预热温度 150~200°C，时间 60~120sec;
- 2、峰值温度 255±5°C，时间持续为 5±0.5sec;
- 3、焊接制程冷却速度为 2~10°C/sec.

Note:

- 1.Preheating:150~200°C, Time:60~120sec.
- 2.Peak Temp.:255±5°C, Duration:5±0.5sec.
3. Cooling Speed: 2~10°C/sec.

耐焊接热试验条件 / Resistance to Soldering Heat Test Conditions

温度：260±5°C

时间：10±1 sec.

Temp.:260±5°C

Time:10±1 sec

包装规格 / Packaging SPEC.

卷盘包装 / REEL

Package Type 封装形式	Units 包装数量					Dimension 包装尺寸 (unit: mm ³)		
	Units/Reel 只/卷盘	Reels/Inner Box 卷盘/盒	Units/Inner Box 只/盒	Inner Boxes/Outer Box 盒/箱	Units/Outer Box 只/箱	Reel	Inner Box 盒	Outer Box 箱
SOT-89	1,000	7	7,000	6	42,000	7" ×12	180×120×180	390×385×205

使用说明 / Notices